

1N4001S THRU 1N4007S

1.0AMP. SILICON RECTIFIERS

FEATURE

- . High current capability
- . Low forward voltage drop
- . Low power loss, high efficiency
- . High surge capability
- . High temperature soldering guaranteed $260^{\circ}\text{C}\ / 10\text{sec}/\ 0.375"$ lead length at 5 lbs tension
- . Ф0.6mm leads

MECHANICAL DATA

. Terminal: Plated axial leads solderable per

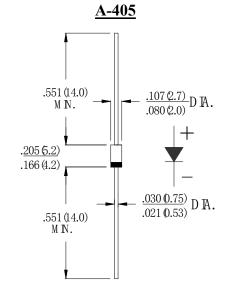
MIL-STD 202E, method 208C

. Case: Molded with UL-94 Class V-0 recognized

Flame Retardant Epoxy

. Polarity: color band denotes cathode

. Mounting position: any



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	SYMBOL	1N 4001S	1N 4002S	1N 4003S	1N 4004S	1N 4005S	1N 4006S	1N 4007S	units
Maximum Recurrent Peak Reverse Voltage	$V_{ m RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	$V_{ m RMS}$	35	70	140	280	420	560	700	V
Maximum DC blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current .375"(9.5mm) lead length at T _A =55°C	I _{F(AV)}	1.0							A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		30.0							A
Maximum Forward Voltage at 1.0A DC	V_{F}	1.0							V
Maximum Forward Voltage at 3.0A DC	V_{F}	1.3							V
Maximum DC Reverse Current $@T_A=25^{\circ}C$ at rated DC blocking voltage $@T_A=100^{\circ}C$	$I_{ m R}$	5.0 100.0							μΑ
Typical Junction Capacitance (Note 1)	C _J 15								pF
Typical Thermal Resistance (Note 2)	$R_{(JA)}$	75							°C/W
Storage Temperature	T _{STG}	-55 to +150							°C
Operation Junction Temperature	$T_{ m J}$	-55 to +150							°C

Note:

- 1. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
- 2. Thermal Resistance from Junction to Ambient at 0.375" (9.5mm) lead length, vertical P.C. Board Mounted.